

WHAT IS CLAIMED IS:

1. A sintered body containing 95 Wt% or more germanium and tungsten.

5 2. A sintered body according to claim 1, wherein a weight ratio of tungsten to germanium lies within a range from 0.01 to 10.

 3. A sintered body according to claim 1,
10 wherein a filling factor of germanium and tungsten is equal to or larger than 60%.

 4. A sintered body according to claim 1,
wherein said sintered body is used as a target of a
15 PVD apparatus.

 5. A sintered body according to claim 4,
wherein said sintered body is used as a target of sputtering.

20 6. A film forming method of a resistance film, whereby the resistance film is formed onto a substrate by sputtering the sintered body according to claim 1.

25 7. A method according to claim 6, wherein the resistance film having predetermined resistivity is

formed by changing a weight ratio of tungsten to germanium of said sintered body.

8. A method according to claim 7, wherein said
5 predetermined resistivity ρ is $\rho = 10^3$ to $10^9 \Omega\text{m}$.

9. A method according to claim 6, wherein said sputtering is executed in a nitrogen atmosphere.

10 10. A manufacturing method of an airtight vessel supporting structure which is arranged in the airtight vessel containing an electron source and an irradiation body to which electrons emitted from said electron source are irradiated, comprising

15 a film forming step of forming a resistance film onto a surface of a substrate,
wherein said film forming step is executed by the film forming method according to claim 6.

20 11. A manufacturing method of an electron generating apparatus in which an electron source and an irradiation body to which electrons emitted from said electron source are irradiated are provided in an airtight vessel, comprising

25 a film forming step of forming a resistance film onto a surface of an insulating member in said airtight vessel,

wherein said film forming step is executed by the film forming method according to claim 6.

12. A manufacturing method of an image
5 displaying apparatus in which an electron source and phosphor to which electrons emitted from said electron source are irradiated are provided in an airtight vessel, comprising
a film forming step of forming a resistance
10 film onto a surface of an insulating member in said airtight vessel,

wherein said film forming step is executed by the film forming method according to claim 6.

15 13. A method according to claim 12, wherein said insulating member is a supporting structure of said airtight vessel.